

Silicon PNP Power Transistors

2SA1262

DESCRIPTION

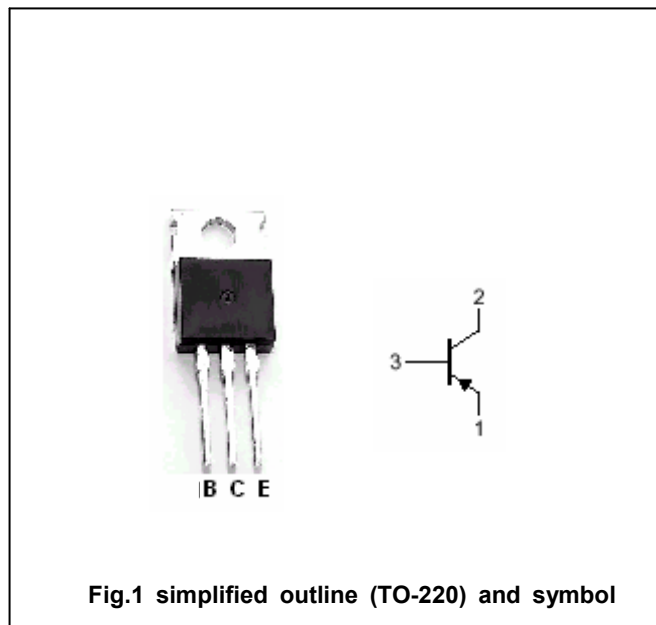
- With TO-220 package
- Complement to type 2SC3179

APPLICATIONS

- Audio and general purpose

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

**Absolute maximum ratings($T_a=25^\circ\text{C}$)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-60	V
V_{CEO}	Collector-emitter voltage	Open base	-60	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-4	A
I_B	Base current		-1	A
P_C	Collector power dissipation	$T_C=25$	30	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

Tj=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-25mA, I_B=0$	-60			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=-2A; I_B=-0.2A$			-0.6	V
I_{CBO}	Collector cut-off current	$V_{CB}=-60V; I_E=0$			-100	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=-6V; I_C=0$			-100	μA
h_{FE}	DC current gain	$I_C=-1A; V_{CE}=-4V$	40			
f_T	Transition frequency	$I_E=0.2A; V_{CE}=-12V$		15		MHz
C_{ob}	Output capacitance	$I_E=0; V_{CB}=-10V; f=1MHz$		90		pF

Switching times

t_{on}	Turn-on time	$I_C=-2A; I_{B1}=-I_{B2}=-0.2A$ $R_L=10\Omega; V_{CC}=-20V$		0.25		μs
t_s	Storage time			0.75		μs
t_f	Fall time			0.25		μs

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Fig.2 Outline dimensions(unindicated tolerance:±0.10 mm)

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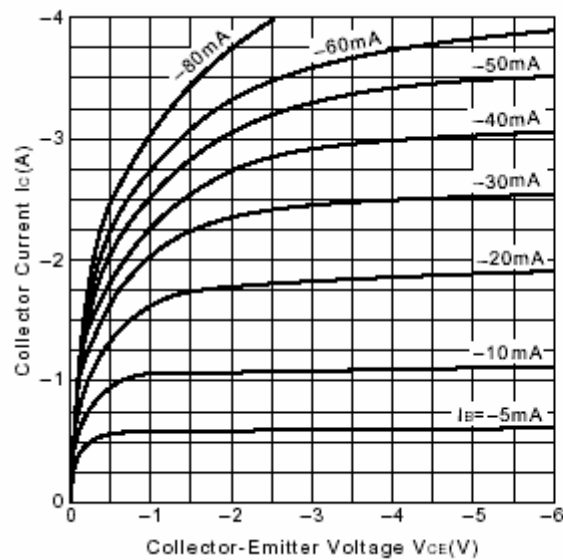


Fig.3 Static Characteristic

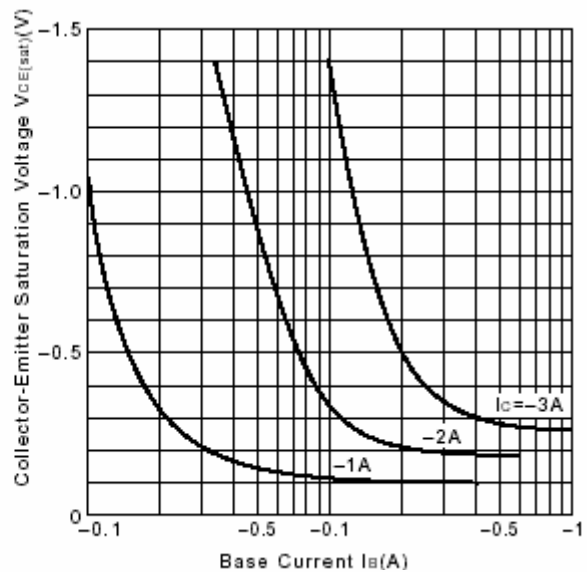
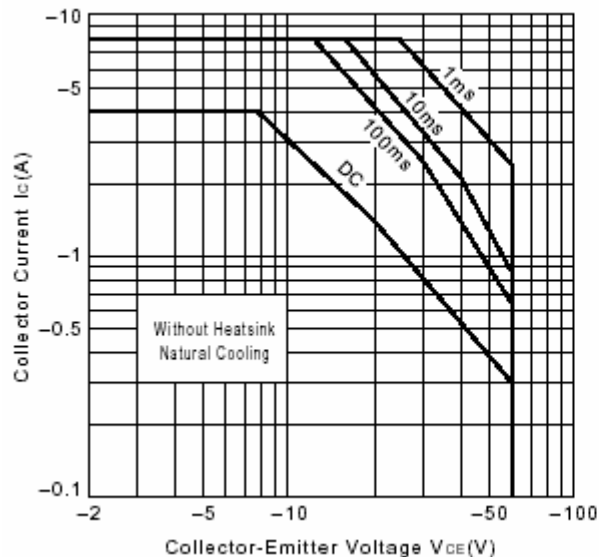
Fig.4 $V_{CE(sat)} - I_B$ Characteristics

Fig.5 Safe Operating Area

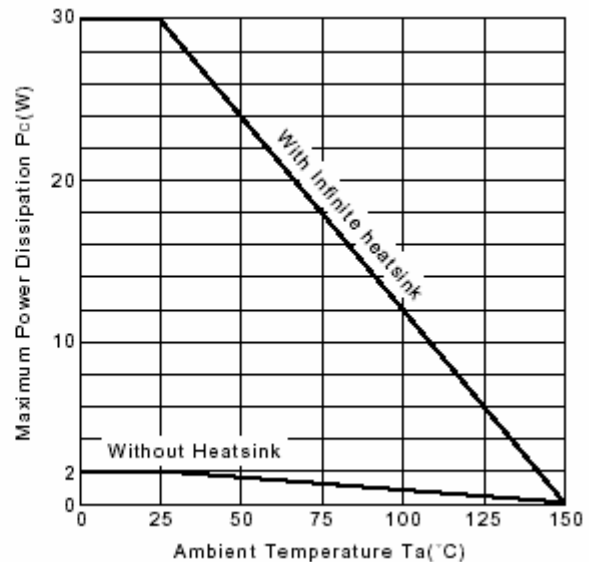
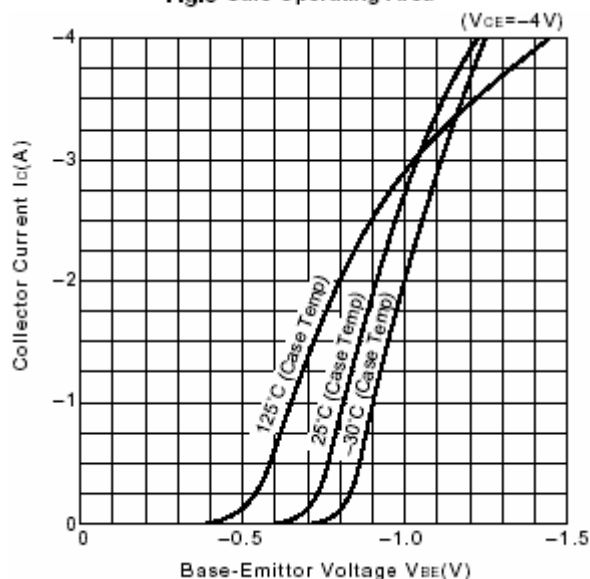
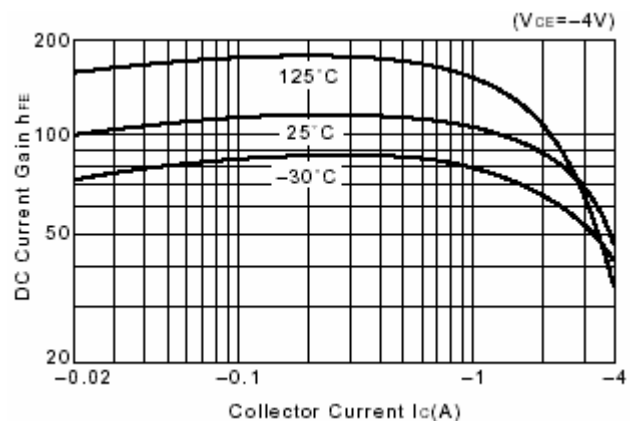
Fig.6 $P_C - T_a$ DeratingFig.7 $I_C - V_{BE}$ 

Fig.8 DC current Gain